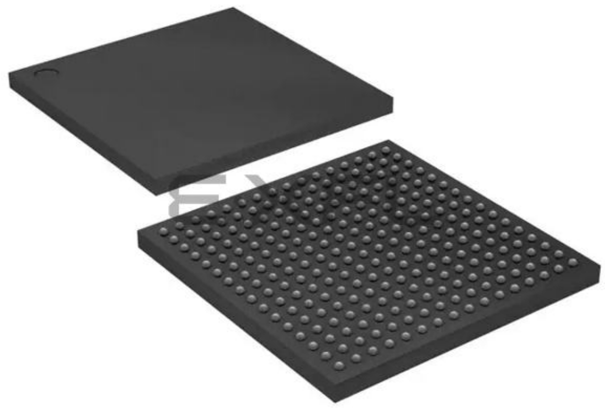

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Understanding Embedded - CPLDs (Complex Programmable Logic Devices)

Embedded - CPLDs, or Complex Programmable Logic Devices, are highly versatile digital logic devices used in electronic systems. These programmable components are designed to perform complex logical operations and can be customized for specific applications. Unlike fixed-function ICs, CPLDs offer the flexibility to reprogram their configuration, making them an ideal choice for various embedded systems. They consist of a set of logic gates and programmable interconnects, allowing designers to implement complex logic circuits without needing custom hardware.

Applications of Embedded - CPLDs

Details	
Product Status	Active
Programmable Type	In System Programmable
Delay Time tpd(1) Max	5.4 ns
Voltage Supply - Internal	1.71V ~ 1.89V
Number of Logic Elements/Blocks	570
Number of Macrocells	440
Number of Gates	-
Number of I/O	160
Operating Temperature	0°C ~ 85°C (TJ)
Mounting Type	Surface Mount
Package / Case	256-BGA
Supplier Device Package	256-FBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epm570gf256c3n

1. Introduction

MII51001-1.9

Introduction

The MAX® II family of instant-on, non-volatile CPLDs is based on a 0.18-µm, 6-layer-metal-flash process, with densities from 240 to 2,210 logic elements (LEs) (128 to 2,210 equivalent macrocells) and non-volatile storage of 8 Kbits. MAX II devices offer high I/O counts, fast performance, and reliable fitting versus other CPLD architectures. Featuring MultiVolt core, a user flash memory (UFM) block, and enhanced in-system programmability (ISP), MAX II devices are designed to reduce cost and power while providing programmable solutions for applications such as bus bridging, I/O expansion, power-on reset (POR) and sequencing control, and device configuration control.

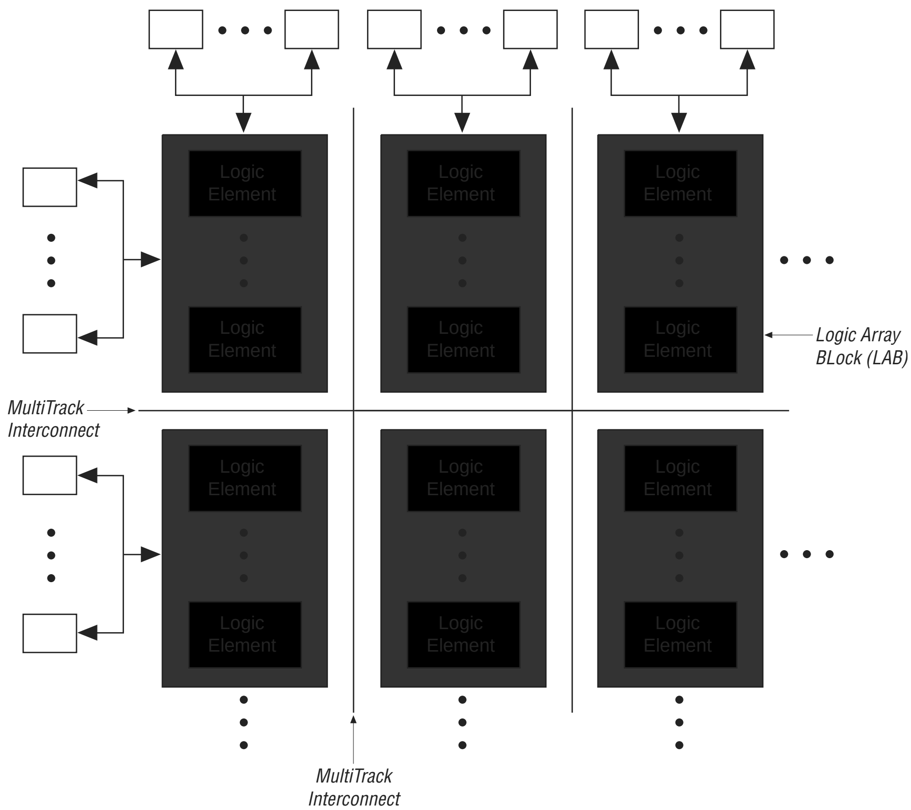
Features

The MAX II CPLD has the following features:

- Low-cost, low-power CPLD
- Instant-on, non-volatile architecture
- Standby current as low as 25 µA
- Provides fast propagation delay and clock-to-output times
- Provides four global clocks with two clocks available per logic array block (LAB)
- UFM block up to 8 Kbits for non-volatile storage
- MultiVolt core enabling external supply voltages to the device of either 3.3 V/2.5 V or 1.8 V
- MultiVolt I/O interface supporting 3.3-V, 2.5-V, 1.8-V, and 1.5-V logic levels
- Bus-friendly architecture including programmable slew rate, drive strength, bus-hold, and programmable pull-up resistors
- Schmitt triggers enabling noise tolerant inputs (programmable per pin)
- I/Os are fully compliant with the Peripheral Component Interconnect Special Interest Group (PCI SIG) PCI Local Bus Specification, Revision 2.2 for 3.3-V operation at 66 MHz
- Supports hot-socketing
- Built-in Joint Test Action Group (JTAG) boundary-scan test (BST) circuitry compliant with IEEE Std. 1149.1-1990
- ISP circuitry compliant with IEEE Std. 1532

Figure 2–1 shows a functional block diagram of the MAX II device.

Figure 2–1. MAX II Device Block Diagram



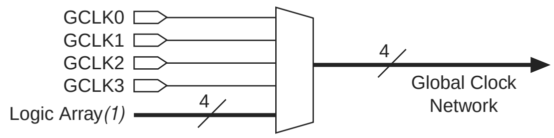
Each MAX II device contains a flash memory block within its floorplan. On the EPM240 device, this block is located on the left side of the device. On the EPM570, EPM1270, and EPM2210 devices, the flash memory block is located on the bottom-left area of the device. The majority of this flash memory storage is partitioned as the dedicated configuration flash memory (CFM) block. The CFM block provides the non-volatile storage for all of the SRAM configuration information. The CFM automatically downloads and configures the logic and I/O at power-up, providing instant-on operation.

For more information about configuration upon power-up, refer to the *Hot Socketing and Power-On Reset in MAX II Devices* chapter in the *MAX II Device Handbook*.

A portion of the flash memory within the MAX II device is partitioned into a small block for user data. This user flash memory (UFM) block provides 8,192 bits of general-purpose user storage. The UFM provides programmable port connections to the logic array for reading and writing. There are three LAB rows adjacent to this block, with column numbers varying by device.

Table 2–1 shows the number of LAB rows and columns in each device, as well as the number of LAB rows and columns adjacent to the flash memory area in the EPM570, EPM1270, and EPM2210 devices. The long LAB rows are full LAB rows that extend from one side of row I/O blocks to the other. The short LAB rows are adjacent to the UFM block; their length is shown as width in LAB columns.

Figure 2–13. Global Clock Generation

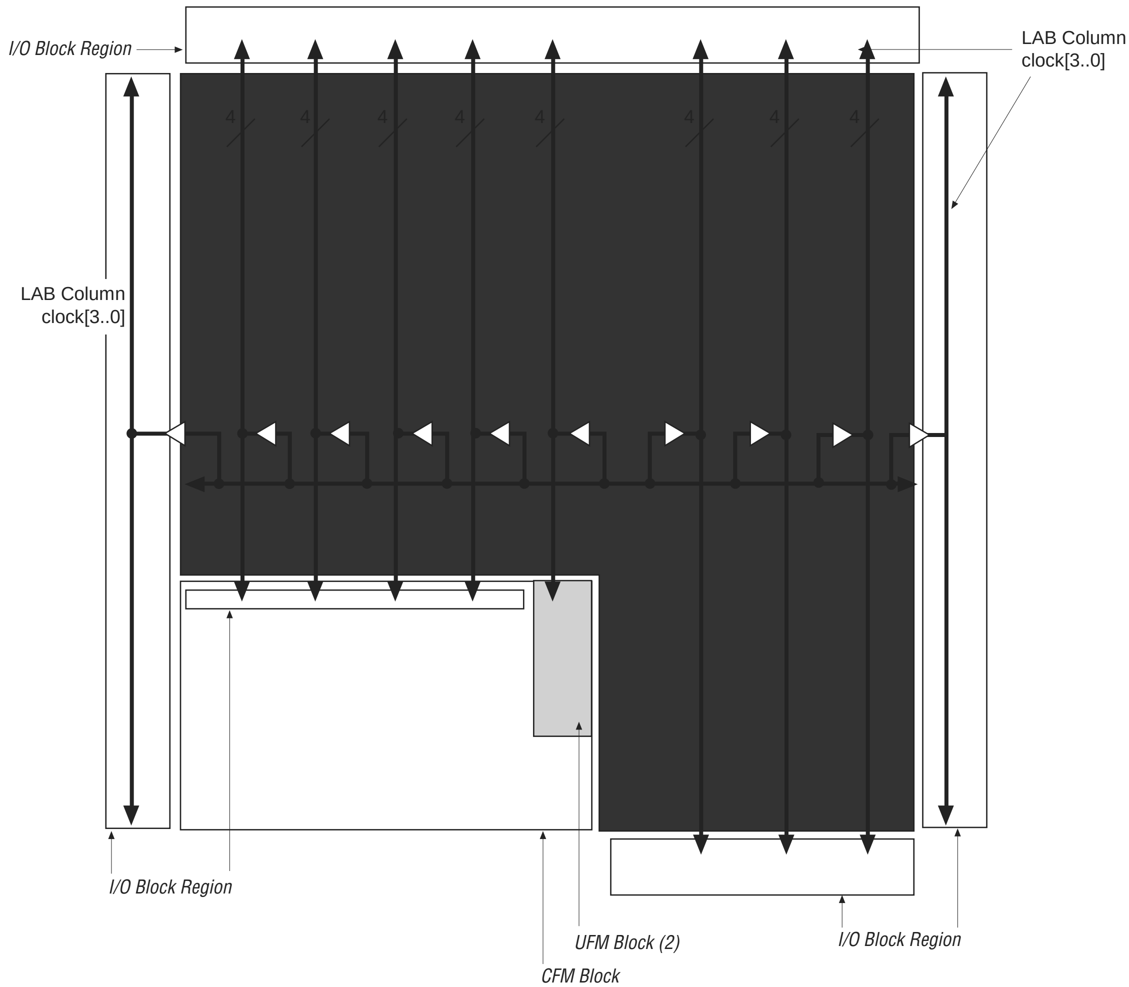


Note to Figure 2–13:

(1) Any I/O pin can use a MultiTrack interconnect to route as a logic array-generated global clock signal.

The global clock network drives to individual LAB column signals, LAB column clocks [3..0], that span an entire LAB column from the top to the bottom of the device. Unused global clocks or control signals in a LAB column are turned off at the LAB column clock buffers shown in Figure 2–14. The LAB column clocks [3..0] are multiplexed down to two LAB clock signals and one LAB clear signal. Other control signal types route from the global clock network into the LAB local interconnect. See "LAB Control Signals" on page 2–5 for more information.

Figure 2–14. Global Clock Network *(Note 1)*



Notes to Figure 2–14:

(1) LAB column clocks in I/O block regions provide high fan-out output enable signals.

(2) LAB column clocks drive to the UFM block.

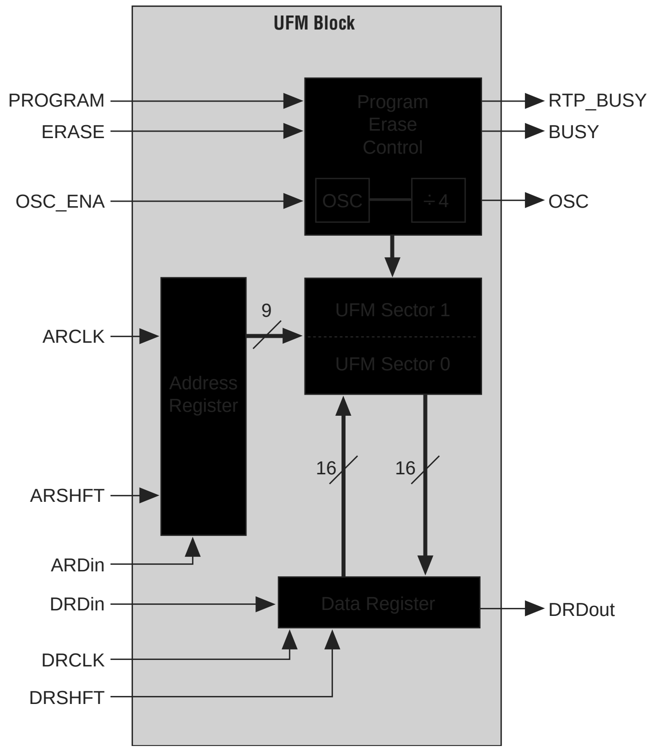
User Flash Memory Block

MAX II devices feature a single UFM block, which can be used like a serial EEPROM for storing non-volatile information up to 8,192 bits. The UFM block connects to the logic array through the MultiTrack interconnect, allowing any LE to interface to the UFM block. Figure 2–15 shows the UFM block and interface signals. The logic array is used to create customer interface or protocol logic to interface the UFM block data outside of the device. The UFM block offers the following features:

- Non-volatile storage up to 16-bit wide and 8,192 total bits
- Two sectors for partitioned sector erase
- Built-in internal oscillator that optionally drives logic array
- Program, erase, and busy signals

- Auto-increment addressing
- Serial interface to logic array with programmable interface

Figure 2–15. UFM Block and Interface Signals



UFM Storage

Each device stores up to 8,192 bits of data in the UFM block. Table 2–3 shows the data size, sector, and address sizes for the UFM block.

Table 2–3. UFM Array Size

Device	Total Bits	Sectors	Address Bits	Data Width
EPM240 EPM570 EPM1270 EPM2210	8,192	2 (4,096 bits/sector)	9	16

There are 512 locations with 9-bit addressing ranging from `000h` to `1FFh`. Sector 0 address space is `000h` to `0FFh` and Sector 1 address space is from `100h` to `1FFh`. The data width is up to 16 bits of data. The Quartus II software automatically creates logic to accommodate smaller read or program data widths. Erasure of the UFM involves individual sector erasing (that is, one erase of sector 0 and one erase of sector 1 is required to erase the entire UFM block). Since sector erase is required before a program or write, having two sectors enables a sector size of data to be left untouched while the other sector is erased and programmed with new data.

Internal Oscillator

As shown in Figure 2–15, the dedicated circuitry within the UFM block contains an oscillator. The dedicated circuitry uses this internally for its read and program operations. This oscillator's divide by 4 output can drive out of the UFM block as a logic interface clock source or for general-purpose logic clocking. The typical `OSC` output signal frequency ranges from 3.3 to 5.5 MHz, and its exact frequency of operation is not programmable.

Program, Erase, and Busy Signals

The UFM block's dedicated circuitry automatically generates the necessary internal program and erase algorithm once the `PROGRAM` or `ERASE` input signals have been asserted. The `PROGRAM` or `ERASE` signal must be asserted until the busy signal deasserts, indicating the UFM internal program or erase operation has completed. The UFM block also supports JTAG as the interface for programming and/or reading.

For more information about programming and erasing the UFM block, refer to the *Using User Flash Memory in MAX II Devices* chapter in the *MAX II Device Handbook*.

Auto-Increment Addressing

The UFM block supports standard read or stream read operations. The stream read is supported with an auto-increment address feature. Deasserting the `ARSHIFT` signal while clocking the `ARCLK` signal increments the address register value to read consecutive locations from the UFM array.

Serial Interface

The UFM block supports a serial interface with serial address and data signals. The internal shift registers within the UFM block for address and data are 9 bits and 16 bits wide, respectively. The Quartus II software automatically generates interface logic in LEs for a parallel address and data interface to the UFM block. Other standard protocol interfaces such as SPI are also automatically generated in LE logic by the Quartus II software.

For more information about the UFM interface signals and the Quartus II LE-based alternate interfaces, refer to the *Using User Flash Memory in MAX II Devices* chapter in the *MAX II Device Handbook*.

UFM Block to Logic Array Interface

The UFM block is a small partition of the flash memory that contains the CFM block, as shown in Figure 2–1 and Figure 2–2. The UFM block for the EPM240 device is located on the left side of the device adjacent to the left most LAB column. The UFM block for the EPM570, EPM1270, and EPM2210 devices is located at the bottom left of the device. The UFM input and output signals interface to all types of interconnects (R4 interconnect, C4 interconnect, and DirectLink interconnect to/from adjacent LAB rows). The UFM signals can also be driven from global clocks, `GCLK[3..0]`. The interface region for the EPM240 device is shown in Figure 2–16. The interface regions for EPM570, EPM1270, and EPM2210 devices are shown in Figure 2–17.

Table 2–4 describes the I/O standards supported by MAX II devices.

Table 2–4. MAX II I/O Standards

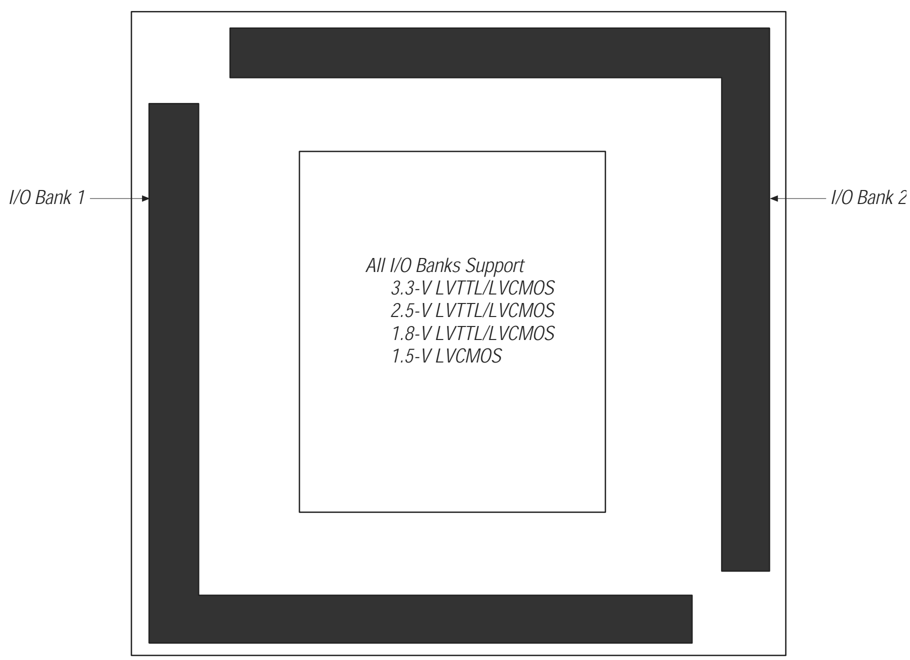
I/O Standard	Type	Output Supply Voltage (VCCIO) (V)
3.3-V LVTTL/LVCMOS	Single-ended	3.3
2.5-V LVTTL/LVCMOS	Single-ended	2.5
1.8-V LVTTL/LVCMOS	Single-ended	1.8
1.5-V LVCMOS	Single-ended	1.5
3.3-V PCI *(1)*	Single-ended	3.3

Note to Table 2–4:

(1) The 3.3-V PCI compliant I/O is supported in Bank 3 of the EPM1270 and EPM2210 devices.

The EPM240 and EPM570 devices support two I/O banks, as shown in Figure 2–22. Each of these banks support all the LVTTL and LVCMOS standards shown in Table 2–4. PCI compliant I/O is not supported in these devices and banks.

Figure 2–22. MAX II I/O Banks for EPM240 and EPM570 *(Note 1)*, *(2)*



Notes to Figure 2–22:

(1) Figure 2–22 is a top view of the silicon die.

(2) Figure 2–22 is a graphical representation only. Refer to the pin list and the Quartus II software for exact pin locations.

The EPM1270 and EPM2210 devices support four I/O banks, as shown in Figure 2–23. Each of these banks support all of the LVTTL and LVCMOS standards shown in Table 2–4. PCI compliant I/O is supported in Bank 3. Bank 3 supports the PCI clamping diode on inputs and PCI drive compliance on outputs. You must use Bank 3 for designs requiring PCI compliant I/O pins. The Quartus II software automatically places I/O pins in this bank if assigned with the PCI I/O standard.

Connect `VCCIO` pins to either a 1.5-V, 1.8 V, 2.5-V, or 3.3-V power supply, depending on the output requirements. The output levels are compatible with systems of the same voltage as the power supply (that is, when `VCCIO` pins are connected to a 1.5-V power supply, the output levels are compatible with 1.5-V systems). When `VCCIO` pins are connected to a 3.3-V power supply, the output high is 3.3 V and is compatible with 3.3-V or 5.0-V systems. Table 2–7 summarizes MAX II MultiVolt I/O support.

Table 2–7. MAX II MultiVolt I/O Support *(Note 1)*

VCCIO (V)	Input Signal					Output Signal				
	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V
1.5	✓	✓	✓	✓	—	✓	—	—	—	—
1.8	✓	✓	✓	✓	—	✓ *(2)*	✓	—	—	—
2.5	—	—	✓	✓	—	✓ *(3)*	✓ *(3)*	✓	—	—
3.3	—	—	✓ *(4)*	✓	✓ *(5)*	✓ *(6)*	✓ *(6)*	✓ *(6)*	✓	✓ *(7)*

Notes to Table 2–7:

(1) To drive inputs higher than V_{CCIO} but less than 4.0 V including the overshoot, disable the I/O clamp diode. However, to drive 5.0-V inputs to the device, enable the I/O clamp diode to prevent V_I from rising above 4.0 V.

(2) When V_{CCIO} = 1.8 V, a MAX II device can drive a 1.5-V device with 1.8-V tolerant inputs.

(3) When V_{CCIO} = 2.5 V, a MAX II device can drive a 1.5-V or 1.8-V device with 2.5-V tolerant inputs.

(4) When V_{CCIO} = 3.3 V and a 2.5-V input signal feeds an input pin, the VCCIO supply current will be slightly larger than expected.

(5) MAX II devices can be 5.0-V tolerant with the use of an external resistor and the internal I/O clamp diode on the EPM1270 and EPM2210 devices.

(6) When V_{CCIO} = 3.3 V, a MAX II device can drive a 1.5-V, 1.8-V, or 2.5-V device with 3.3-V tolerant inputs.

(7) When V_{CCIO} = 3.3 V, a MAX II device can drive a device with 5.0-V TTL inputs but not 5.0-V CMOS inputs. In the case of 5.0-V CMOS, open-drain setting with internal I/O clamp diode (available only on EPM1270 and EPM2210 devices) and external resistor is required.

For information about output pin source and sink current guidelines, refer to the *AN 428: MAX II CPLD Design Guidelines*.

Referenced Documents

This chapter referenced the following documents:

- *AN 428: MAX II CPLD Design Guidelines*
- *DC and Switching Characteristics* chapter in the *MAX II Device Handbook*
- *Hot Socketing and Power-On Reset in MAX II Devices* chapter in the *MAX II Device Handbook*
- *Using User Flash Memory in MAX II Devices* chapter in the *MAX II Device Handbook*

Document Revision History

Table 2–8 shows the revision history for this chapter.

Table 2–8. Document Revision History

Date and Revision	Changes Made	Summary of Changes
October 2008, version 2.2	■ Updated Table 2–4 and Table 2–6. ■ Updated "I/O Standards and Banks" section. ■ Updated New Document Format.	—
March 2008, version 2.1	■ Updated "Schmitt Trigger" section.	—
December 2007, version 2.0	■ Updated "Clear and Preset Logic Control" section. ■ Updated "MultiVolt Core" section. ■ Updated "MultiVolt I/O Interface" section. ■ Updated Table 2–7. ■ Added "Referenced Documents" section.	Updated document with MAX IIZ information.
December 2006, version 1.7	■ Minor update in "Internal Oscillator" section. Added document revision history.	—
August 2006, version 1.6	■ Updated functional description and I/O structure sections.	—
July 2006, vervion 1.5	■ Minor content and table updates.	—
February 2006, version 1.4	■ Updated "LAB Control Signals" section. ■ Updated "Clear and Preset Logic Control" section. ■ Updated "Internal Oscillator" section. ■ Updated Table 2–5.	—
August 2005, version 1.3	■ Removed Note 2 from Table 2-7.	—
December 2004, version 1.2	■ Added a paragraph to page 2-15.	—
June 2004, version 1.1	■ Added CFM acronym. Corrected Figure 2-19.	—

Power-Up Characteristics

When power is applied to a MAX II device, the POR circuit monitors V_{CCINT} and begins SRAM download at an approximate voltage of 1.7 V or 1.55 V for MAX IIG and MAX IIZ devices. From this voltage reference, SRAM download and entry into user mode takes 200 to 450 µs maximum, depending on device density. This period of time is specified as t_{CONFIG} in the power-up timing section of the *DC and Switching Characteristics* chapter in the *MAX II Device Handbook*.

Entry into user mode is gated by whether all V_{CCIO} banks are powered with sufficient operating voltage. If V_{CCIN}T and V_{CCIO} are powered simultaneously, the device enters user mode within the t_{CONFIG} specifications. If V_{CCIO} is powered more than t_{CONFIG} after V_{CCINT}, the device does not enter user mode until 2 µs after all V_{CCIO} banks are powered.

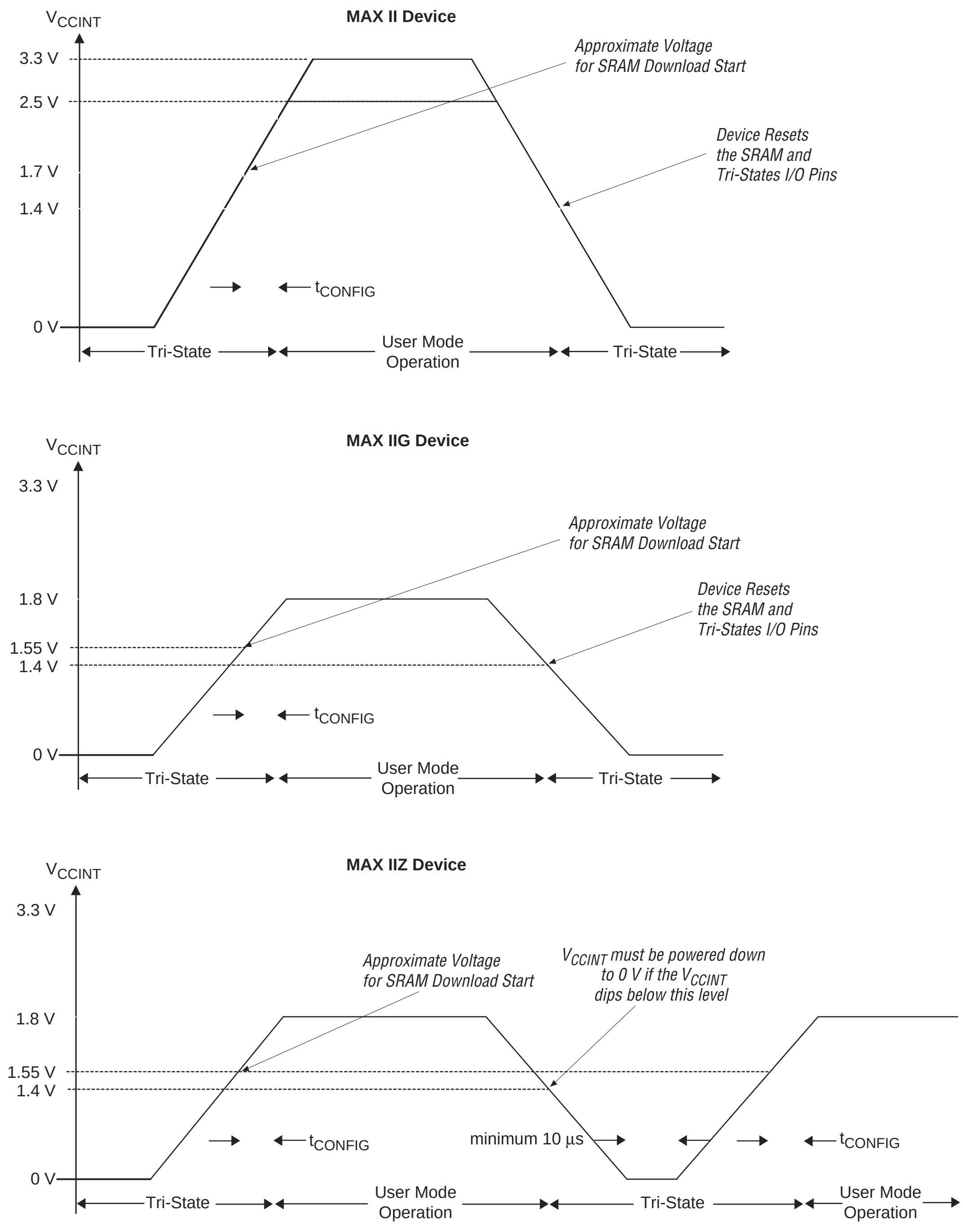
For MAX II and MAX IIG devices, when in user mode, the POR circuitry continues to monitor the V_{CCINT} (but not V_{CCIO}) voltage level to detect a brown-out condition. If there is a V_{CCINT} voltage sag at or below 1.4 V during user mode, the POR circuit resets the SRAM and tri-states the I/O pins. Once V_{CCINT} rises back to approximately 1.7 V (or 1.55 V for MAX IIG devices), the SRAM download restarts and the device begins to operate after t_{CONFIG} time has passed.

For MAX IIZ devices, the POR circuitry does not monitor the V_{CCINT} and V_{CCIO} voltage levels after the device enters user mode. If there is a V_{CCINT} voltage sag below 1.4 V during user mode, the functionality of the device will not be guaranteed and you must power down the V_{CCINT} to 0 V for a minimum of 10 µs before powering the V_{CCINT} and V_{CCIO} up again. Once V_{CCINT} rises from 0 V back to approximately 1.55 V, the SRAM download restarts and the device begins to operate after t_{CONFIG} time has passed.

Figure 4–5 shows the voltages for POR of MAX II, MAX IIG, and MAX IIZ devices during power-up into user mode and from user mode to power-down or brown-out.

☞ All V_{CCINT} and V_{CCIO} pins of all banks must be powered on MAX II devices before entering user mode.

Figure 4–5. Power-Up Characteristics for MAX II, MAX IIG, and MAX IIZ Devices *(Note 1)*, *(2)*



Notes to Figure 4–5:

(1) Time scale is relative.

(2) Figure 4–5 assumes all V_{CCIO} banks power up simultaneously with the V_{CCINT} profile shown. If not, t_{CONFIG} stretches out until all V_{CCIO} banks are powered.

☞ After SRAM configuration, all registers in the device are cleared and released into user function before I/O tri-states are released. To release clears after tri-states are released, use the `DEV_CLRn` pin option. To hold the tri-states beyond the power-up configuration time, use the `DEV_OE` pin option.

Referenced Documents

This chapter refereces the following documents:

- *DC and Switching Characteristics* chapter in the *MAX II Device Handbook*
- *Using MAX II Devices in Multi-Voltage Systems* chapter in the *MAX II Device Handbook*

Document Revision History

Table 4–1 shows the revision history for this chapter.

Table 4–1. Document Revision History

Date and Revision	Changes Made	Summary of Changes
October 2008, version2.1	■ Updated "MAX II Hot-Socketing Specifications" and "Power-On Reset Circuitry" sections. ■ Updated New Document Format.	—
December 2007, version 2.0	■ Updated "Hot Socketing Feature Implementation in MAX II Devices" section. ■ Updated "Power-On Reset Circuitry" section. ■ Updated Figure 4–5. ■ Added "Referenced Documents" section.	Updated document with MAX IIZ information.
December 2006, version 1.5	■ Added document revision history.	—
February 2006, version 1.4	■ Updated "MAX II Hot-Socketing Specifications" section. ■ Updated "AC and DC Specifications" section. ■ Updated "Power-On Reset Circuitry" section.	—
June 2005, version 1.3	■ Updated AC and DC specifications on page 4-2.	—
December 2004, version 1.2	■ Added content to Power-Up Characteristics section. ■ Updated Figure 4-5.	—
June 2004, version 1.1	■ Corrected Figure 4-2.	—

Programming/Erasure Specifications

Table 5–3 shows the MAX II device family programming/erasure specifications.

Table 5–3. MAX II Device Programming/Erasure Specifications

Parameter	Minimum	Typical	Maximum	Unit
Erase and reprogram cycles	—	—	100 *(1)*	Cycles

Note to Table 5–3:

(1) This specification applies to the UFM and configuration flash memory (CFM) blocks.

DC Electrical Characteristics

Table 5–4 shows the MAX II device family DC electrical characteristics.

Table 5–4. MAX II Device DC Electrical Characteristics *(Note 1)* (Part 1 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
I_I	Input pin leakage current	$V_I = V_{CCIO}$max to 0 V *(2)*	–10	—	10	µA
I_{OZ}	Tri-stated I/O pin leakage current	$V_O = V_{CCIO}$max to 0 V *(2)*	–10	—	10	µA
$I_{CCSTANDBY}$	V_{CCINT} supply current (standby) *(3)*	MAX II devices	—	12	—	mA
		MAX IIG devices	—	2	—	mA
		EPM240Z (Commercial grade) *(4)*	—	25	90	µA
		EPM240Z (Industrial grade) *(5)*	—	25	139	µA
		EPM570Z (Commercial grade) *(4)*	—	27	96	µA
		EPM570Z (Industrial grade) *(5)*	—	27	152	µA
$V_{SCHMITT}$ *(6)*	Hysteresis for Schmitt trigger input *(7)*	V_{CCIO} = 3.3 V	—	400	—	mV
		V_{CCIO} = 2.5 V	—	190	—	mV
$I_{CCPOWERUP}$	V_{CCINT} supply current during power-up *(8)*	MAX II devices	—	55	—	mA
		MAX IIG and MAX IIZ devices	—	40	—	mA
R_{PULLUP}	Value of I/O pin pull-up resistor during user mode and in-system programming	V_{CCIO} = 3.3 V *(9)*	5	—	25	kΩ
		V_{CCIO} = 2.5 V *(9)*	10	—	40	kΩ
		V_{CCIO} = 1.8 V *(9)*	25	—	60	kΩ
		V_{CCIO} = 1.5 V *(9)*	45	—	95	kΩ

Table 5–6. 3.3-V LVCMOS Specifications (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{OH}	High-level output voltage	V_{CCIO} = 3.0, IOH = –0.1 mA *(1)*	V_{CCIO} – 0.2	—	V
V_{OL}	Low-level output voltage	V_{CCIO} = 3.0, IOL = 0.1 mA *(1)*	—	0.2	V

Table 5–7. 2.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	2.375	2.625	V
V_{IH}	High-level input voltage	—	1.7	4.0	V
V_{IL}	Low-level input voltage	—	–0.5	0.7	V
V_{OH}	High-level output voltage	IOH = –0.1 mA *(1)*	2.1	—	V
		IOH = –1 mA *(1)*	2.0	—	V
		IOH = –2 mA *(1)*	1.7	—	V
V_{OL}	Low-level output voltage	IOL = 0.1 mA *(1)*	—	0.2	V
		IOL = 1 mA *(1)*	—	0.4	V
		IOL = 2 mA *(1)*	—	0.7	V

Table 5–8. 1.8-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	1.71	1.89	V
V_{IH}	High-level input voltage	—	0.65 × V_{CCIO}	2.25 *(2)*	V
V_{IL}	Low-level input voltage	—	–0.3	0.35 × V_{CCIO}	V
V_{OH}	High-level output voltage	IOH = –2 mA *(1)*	V_{CCIO} – 0.45	—	V
V_{OL}	Low-level output voltage	IOL = 2 mA *(1)*	—	0.45	V

Table 5–9. 1.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	1.425	1.575	V
V_{IH}	High-level input voltage	—	0.65 × V_{CCIO}	V_{CCIO} + 0.3 *(2)*	V
V_{IL}	Low-level input voltage	—	–0.3	0.35 × V_{CCIO}	V
V_{OH}	High-level output voltage	IOH = –2 mA *(1)*	0.75 × V_{CCIO}	—	V
V_{OL}	Low-level output voltage	IOL = 2 mA *(1)*	—	0.25 × V_{CCIO}	V

Notes to Table 5–5 through Table 5–9:

(1) This specification is supported across all the programmable drive strength settings available for this I/O standard, as shown in the *MAX II Architecture* chapter (*I/O Structure section*) in the *MAX II Device Handbook*.

(2) This maximum V_{IH} reflects the JEDEC specification. The MAX II input buffer can tolerate a V_{IH} maximum of 4.0, as specified by the V_I parameter in Table 5–2.

Table 5–10. 3.3-V PCI Specifications *(Note 1)*

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	3.0	3.3	3.6	V
V_{IH}	High-level input voltage	—	0.5 × V_{CCIO}	—	V_{CCIO} + 0.5	V
V_{IL}	Low-level input voltage	—	–0.5	—	0.3 × V_{CCIO}	V
V_{OH}	High-level output voltage	IOH = –500 µA	0.9 × V_{CCIO}	—	—	V
V_{OL}	Low-level output voltage	IOL = 1.5 mA	—	—	0.1 × V_{CCIO}	V

Note to Table 5–10:

(1) 3.3-V PCI I/O standard is only supported in Bank 3 of the EPM1270 and EPM2210 devices.

Bus Hold Specifications

Table 5–11 shows the MAX II device family bus hold specifications.

Table 5–11. Bus Hold Specifications

Parameter	Conditions	V_{CCIO} Level								Unit
		1.5 V		1.8 V		2.5 V		3.3 V		
		Min	Max	Min	Max	Min	Max	Min	Max	
Low sustaining current	$V_{IN} > V_{IL}$ (maximum)	20	—	30	—	50	—	70	—	µA
High sustaining current	$V_{IN} < V_{IH}$ (minimum)	–20	—	–30	—	–50	—	–70	—	µA
Low overdrive current	0 V < V_{IN} < V_{CCIO}	—	160	—	200	—	300	—	500	µA
High overdrive current	0 V < V_{IN} < V_{CCIO}	—	–160	—	–200	—	–300	—	–500	µA

Table 5–20. t_{XZ} IOE Microparameter Adders for Slow Slew Rate

Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTL	16 mA	—	206	—	–20	—	–247	—	1,433	—	1,446	—	1,454	ps
	8 mA	—	891	—	665	—	438	—	1,332	—	1,345	—	1,348	ps
3.3-V LVCMOS	8 mA	—	206	—	–20	—	–247	—	1,433	—	1,446	—	1,454	ps
	4 mA	—	891	—	665	—	438	—	1,332	—	1,345	—	1,348	ps
2.5-V LVTTL / LVCMOS	14 mA	—	222	—	–4	—	–231	—	213	—	208	—	213	ps
	7 mA	—	943	—	717	—	490	—	166	—	161	—	166	ps
3.3-V PCI	20 mA	—	161	—	210	—	258	—	1,332	—	1,345	—	1,348	ps

The default slew rate setting for MAX II devices in the Quartus II design software is "fast".

Table 5–21. UFM Block Internal Timing Microparameters (Part 1 of 3)

Symbol	Parameter	MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t_{ACLK}	Address register clock period	100	—	100	—	100	—	100	—	100	—	100	—	ns
t_{ASU}	Address register shift signal setup to address register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{AH}	Address register shift signal hold to address register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{ADS}	Address register data in setup to address register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{ADH}	Address register data in hold from address register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{DCLK}	Data register clock period	100	—	100	—	100	—	100	—	100	—	100	—	ns
t_{DSS}	Data register shift signal setup to data register clock	60	—	60	—	60	—	60	—	60	—	60	—	ns
t_{DSH}	Data register shift signal hold from data register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns

Table 5–29. External Timing Output Delay and t_{OD} Adders for Fast Slew Rate

I/O Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTL	16 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	8 mA	—	65	—	84	—	104	—	–6	—	–2	—	–3	ps
3.3-V LVCMOS	8 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	4 mA	—	65	—	84	—	104	—	–6	—	–2	—	–3	ps
2.5-V LVTTL / LVCMOS	14 mA	—	122	—	158	—	195	—	–63	—	–71	—	–88	ps
	7 mA	—	193	—	251	—	309	—	10	—	–1	—	1	ps
1.8-V LVTTL / LVCMOS	6 mA	—	568	—	738	—	909	—	128	—	118	—	118	ps
	3 mA	—	654	—	850	—	1,046	—	352	—	327	—	332	ps
1.5-V LVCMOS	4 mA	—	1,059	—	1,376	—	1,694	—	421	—	400	—	400	ps
	2 mA	—	1,167	—	1,517	—	1,867	—	757	—	743	—	743	ps
3.3-V PCI	20 mA	—	3	—	4	—	5	—	–6	—	–2	—	–3	ps

Table 5–30. External Timing Output Delay and t_{OD} Adders for Slow Slew Rate

I/O Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTL	16 mA	—	7,064	—	6,745	—	6,426	—	5,966	—	5,992	—	6,118	ps
	8 mA	—	7,946	—	7,627	—	7,308	—	6,541	—	6,570	—	6,720	ps
3.3-V LVCMOS	8 mA	—	7,064	—	6,745	—	6,426	—	5,966	—	5,992	—	6,118	ps
	4 mA	—	7,946	—	7,627	—	7,308	—	6,541	—	6,570	—	6,720	ps
2.5-V LVTTL / LVCMOS	14 mA	—	10,434	—	10,115	—	9,796	—	9,141	—	9,154	—	9,297	ps
	7 mA	—	11,548	—	11,229	—	10,910	—	9,861	—	9,874	—	10,037	ps
1.8-V LVTTL / LVCMOS	6 mA	—	22,927	—	22,608	—	22,289	—	21,811	—	21,854	—	21,857	ps
	3 mA	—	24,731	—	24,412	—	24,093	—	23,081	—	23,034	—	23,107	ps
1.5-V LVCMOS	4 mA	—	38,723	—	38,404	—	38,085	—	39,121	—	39,124	—	39,124	ps
	2 mA	—	41,330	—	41,011	—	40,692	—	40,631	—	40,634	—	40,634	ps
3.3-V PCI	20 mA	—	261	—	339	—	418	—	6,644	—	6,627	—	6,914	ps

Table 5–31. MAX II IOE Programmable Delays

Parameter	MAX II / MAX IIG						MAX IIZ						Unit
	–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Input Delay from Pin to Internal Cells = 1	—	1,225	—	1,592	—	1,960	—	1,858	—	2,171	—	2,214	ps
Input Delay from Pin to Internal Cells = 0	—	89	—	115	—	142	—	569	—	609	—	616	ps

Maximum Input and Output Clock Rates

Table 5–32 and Table 5–33 show the maximum input and output clock rates for standard I/O pins in MAX II devices.

Table 5–32. MAX II Maximum Input Clock Rate for I/O

I/O Standard		MAX II / MAX IIG			MAX IIZ			Unit
		–3 Speed Grade	–4 Speed Grade	–5 Speed Grade	–6 Speed Grade	–7 Speed Grade	–8 Speed Grade	
3.3-V LVTTL	Without Schmitt Trigger	304	304	304	304	304	304	MHz
	With Schmitt Trigger	250	250	250	250	250	250	MHz
3.3-V LVCMOS	Without Schmitt Trigger	304	304	304	304	304	304	MHz
	With Schmitt Trigger	250	250	250	250	250	250	MHz
2.5-V LVTTL	Without Schmitt Trigger	220	220	220	220	220	220	MHz
	With Schmitt Trigger	188	188	188	188	188	188	MHz
2.5-V LVCMOS	Without Schmitt Trigger	220	220	220	220	220	220	MHz
	With Schmitt Trigger	188	188	188	188	188	188	MHz
1.8-V LVTTL	Without Schmitt Trigger	200	200	200	200	200	200	MHz
1.8-V LVCMOS	Without Schmitt Trigger	200	200	200	200	200	200	MHz
1.5-V LVCMOS	Without Schmitt Trigger	150	150	150	150	150	150	MHz
3.3-V PCI	Without Schmitt Trigger	304	304	304	304	304	304	MHz

Table 5–35. Document Revision History (Part 2 of 2)

Date and Revision	Changes Made	Summary of Changes
June 2005, version 1.3	■ Updated the R_{PULLUP} parameter in Table 5-4. ■ Added Note 2 to Tables 5-8 and 5-9. ■ Updated Table 5-13. ■ Added "Output Drive Characteristics" section. ■ Added I^2C mode and Notes 5 and 6 to Table 5-14. ■ Updated timing values to Tables 5-14 through 5-33.	—
December 2004, version 1.2	■ Updated timing Tables 5-2, 5-4, 5-12, and Tables 15-14 through 5-34. ■ Table 5-31 is new.	—
June 2004, version 1.1	■ Updated timing Tables 5-15 through 5-32.	—

